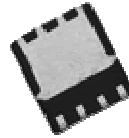


## N-Channel 80-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

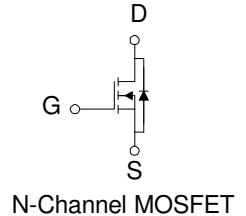
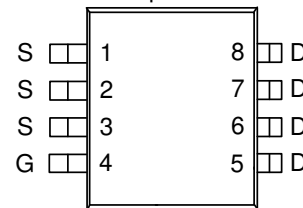
- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology



PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ m( $\Omega$ )	$I_D$ (A)
80	35 @ $V_{GS} = 10V$	9
	40 @ $V_{GS} = 4.5V$	8

DFN3x3-8PP

Top View



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	80	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	$\pm 9$	A
	$T_A = 70^\circ\text{C}$		$\pm 7$	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	$\pm 75$	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	16	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3.5	W
	$T_A = 70^\circ\text{C}$		2	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case <sup>a</sup>	$t \leq 5 \text{ sec}$	$R_{\theta JC}$	25	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 5 \text{ sec}$	$R_{\theta JA}$	50	$^\circ\text{C/W}$

### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

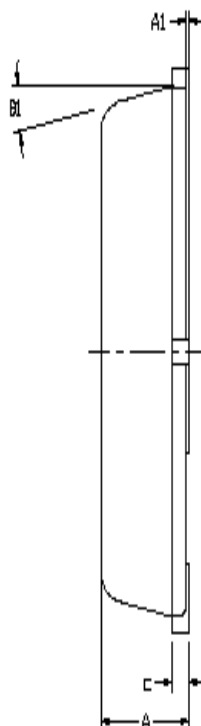
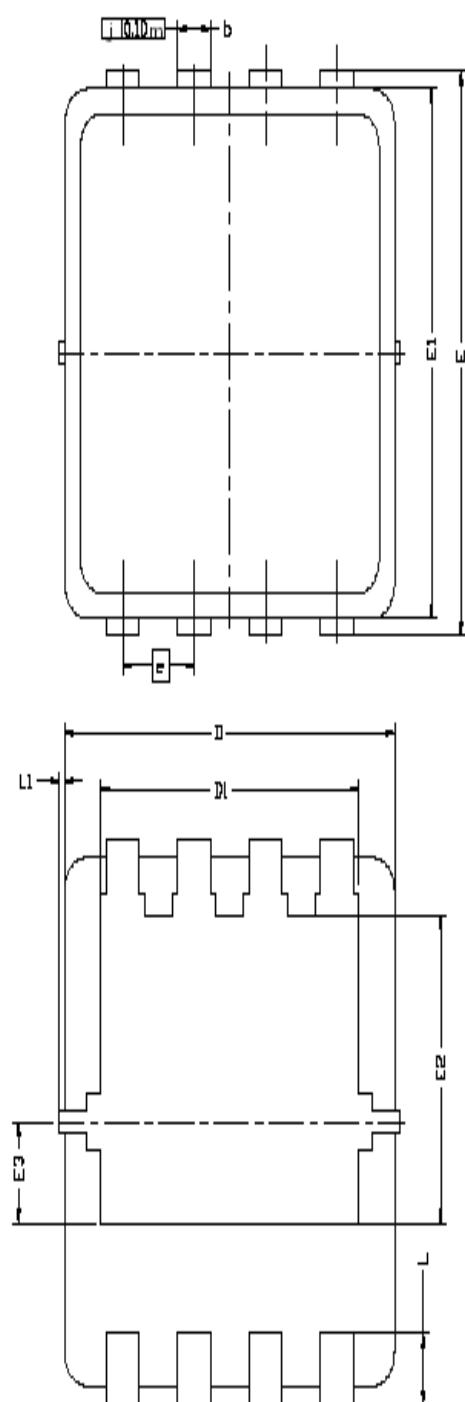
SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 uA	1			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V			1	uA
		V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			25	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	20			A
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1 A			35	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1 A			40	
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 9 A		40		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 2.3 A, V <sub>GS</sub> = 0 V		0.7		V
Dynamic <sup>b</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9 A		28		nC
Gate-Source Charge	Q <sub>gs</sub>			13		
Gate-Drain Charge	Q <sub>gd</sub>			6		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 25 V, R <sub>L</sub> = 25 Ω , I <sub>D</sub> = 1 A, V <sub>GEN</sub> = 10 V		6		nS
Rise Time	t <sub>r</sub>			2		
Turn-Off Delay Time	t <sub>d(off)</sub>			24		
Fall-Time	t <sub>f</sub>			2		

## Notes

- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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## Package Information



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0	---	0.100	0	---	0.004
B1	0°	10°	12°	0°	10°	12°